OIPE PAGE 1 of 2 FORM PTO-1449 (Modified) ATTY. DOCKET NO. SERIAL NO. OCT 2 7 2005 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANTS INFORMATION DISCLOSURE STATEMENT. 10/709,999 FIS920040017US1 APPLICANT: Abraham et al. GROUP: FILING DATE: (Use several sheets if necessary) 2818 June 11, 2004 REFERENCE DESIGNATION U.S. PATENT DOCUMENTS **FILING DATE** ISSUED DOCUMENT **EXAMINER SUBCLASS** (IF APPRO.) **CLASS** NAME INITIALS NUMBER DATE 5,792,569 08/11/1998 Sun et al. AA 5,946,228 08/31/1999 Abraham et. al. AB 6,034,887 03/07/2000 Gupta et al. AC 6,072,718 06/06/2000 Abraham et al. AD 6,104,633 08/15/2000 Abraham et al. ΑE 6,299,991 B1 10/09/2001 Bojarczuk, Jr. et al. AF 6,333,067 B2 12/25/2001 Bojarczuk, Jr. et al. AG 6,385,082 B1 05/07/2002 Abraham et al. AH 6,452,764 B1 09/17/2002 Abraham et. al. Αl 6,538,919 B1 03/25/2003 Abraham et al. AJ 6,660,568 B1 12/09/2003 Gaidis AK 6,784,091 B1 08/31/2004 Nuetzel et al. AL 6,812,141 B1 11/02/2004 Gaidis et al. AM 2003/0198113 A1 10/23/2003 Abraham et al. AN 01/01/2004Abraham et al. 2004/0001350 A1 AO 2004/0051522 A1 03/18/2004/Worledge et al AP 2004/0252559 A1 12/16/2004 Gupta AQ 2004/0253437 A1 12/16/2004 Ingvarsson et al. AR 2005/0050399 A1 03/03/2005 Abraham et al. AS 2005/0079647 A1 04/14/2005 Abraham et al. AT 04/14/2005 Sarma et al. 2005/0079683 A1 AU 2005/0087519 A1 04/28/2005 Klostermann et al. ΑV 2005/0088875 A1 04/28/2005 Abraham et al. AW 2005/0102581 A1 05/12/2005 Abraham et al. AX 2005/0127418 A1 06/16/2005 Abraham AY 2005/0151552 A1 07/14/2005 Abraham et al. AZ 2005/0185458 A1 08/25/2005 Abraham BA

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